

L Number	Hits	Search Text	DB	Time stamp
1	55	156/345.13.ccls.	USPAT	2004/01/07 10:48
2	890	((dress\$3 clean\$3 condition\$3) with (pad cloth)) same (CMP "chemical mechanical")	USPAT	2004/01/07 12:56
3	114	((((dress\$3 clean\$3 condition\$3) with (pad cloth)) same (CMP "chemical mechanical")) and ((analy\$3 monitor\$3 test\$3) with (condition\$3 dress\$3 clean\$3)))	USPAT	2004/01/07 12:57
-	274	156/345.12 156/345.13 156/345.16	USPAT	2003/09/04 10:29
-	13915	(polishing planariz\$5) same (grind\$3 condition\$3)	USPAT	2003/09/04 10:30
-	1270	("chemical mechanical" adj (polishing planariz\$5) same (grind\$3 condition\$3))	USPAT	2003/09/04 10:32
-	0	((("chemical mechanical" adj (polishing planariz\$5) same (grind\$3 condition\$3))) same ((analyz\$3 monitor\$3) adj3 (slurry solution)))	USPAT	2003/09/04 10:34
-	10	((("chemical mechanical" adj (polishing planariz\$5) same (grind\$3 condition\$3))) same ((analyz\$3 monitor\$3) same (slurry solution)))	USPAT	2003/09/04 10:42
-	3517	("ammonium citrate" "nitric acid") same (cu copper)	USPAT	2003/09/04 10:48
-	559	((("ammonium citrate" "nitric acid") same (cu copper)) and (polish\$3 abrad\$3 planariz\$5))	USPAT	2003/09/04 10:49
-	53	chopra-dinesh.in. meikle-scott.in.	USPAT	2003/09/04 12:59
-	1111	micron.as. and (condition\$3 dress\$3) and (analy\$4 monitor\$3)	USPAT	2003/09/04 13:00
-	261	micron.as. and (condition\$3 dress\$3) same (analy\$4 monitor\$3)	USPAT	2003/09/04 14:10
-	305	(polish\$3 abrad\$3) same (gas air) same (spring)	USPAT	2003/09/04 14:12
-	2	("chemical mechanical" adj (polish\$3 abrad\$3)) same (gas air) same (spring)	USPAT	2003/09/04 14:32
-	2422	((("chemical mechanical" adj (polish\$3 abrad\$3)) same (dry plasma)	USPAT	2003/09/04 14:17
-	70	((("chemical mechanical" adj (polish\$3 abrad\$3)) same (dry plasma)) and (spring or "pressure releasing"))	USPAT	2003/09/04 14:17
-	3598	((dry plasma) same (polish\$3 abrad\$3 planari\$5))	EPO; JPO; DERWENT	2003/09/04 14:33
-	654	((dry plasma) adj5 (polish\$3 abrad\$3 planari\$5))	EPO; JPO; DERWENT	2003/09/04 14:33
-	143	((((dry plasma) adj5 (polish\$3 abrad\$3 planari\$5))) and (wafer semiconductor)	EPO; JPO; DERWENT	2003/09/04 14:50
-	11	((((dry plasma) adj5 (polish\$3 abrad\$3 planari\$5))) and (wafer semiconductor) and (spring pressure))	USPAT; EPO; JPO; DERWENT	2003/09/04 14:51
-	1138	134/113 134/104.1	USPAT	2003/09/05 14:41
-	21	(134/113 134/104.1) and (dress\$3 grind\$3 condition\$3 clean\$3) near5 (pad cloth platen)	USPAT	2003/09/05 14:41